

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:
 - a polymer compound produced by addition polymerization having an epoxy group;
 - a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; ~~and~~
 - ~~a solvent;~~ a solvent; and
 - a light absorbing compound.wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.
3. (Previously Presented) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:
 - an s-triazine trione skeleton compound with a molecular weight of 2000 or less having at least two epoxy groups;
 - a polymer compound having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride structure; and
 - a solvent,wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

4. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a solvent; and

a polymer compound having ~~a carboxyl group or a protected carboxyl group,~~
group and an epoxy group,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

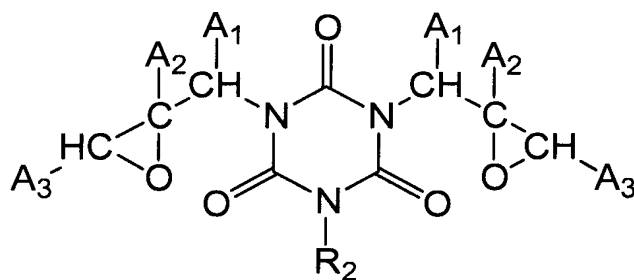
5. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a carboxyl group is a compound having acrylic acid or methacrylic acid as a unit structure.

6. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a phenolic hydroxyl group is a compound having hydroxystyrene as a unit structure.

7. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound having at least three epoxy groups and no aromatic ring structure.

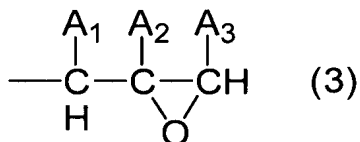
8. (Canceled)

9. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound of formula (2)



(2)

wherein A₁, A₂ and A₃ each are hydrogen atom, methyl group or ethyl group, R₂ is hydrogen atom, C₁₋₆ alkyl group, C₃₋₆ alkenyl group, benzyl group, phenyl group or a group of formula (3)



(3)

10-12. (Canceled)

13. (Currently Amended) A method for forming photoresist ~~pattern-patterns~~ for use in manufacture of semiconductor ~~device-devices~~, comprising

coating ~~the-an~~ underlayer forming composition ~~according to claim 2~~ on a semiconductor substrate, and baking it to form an underlayer coating,

forming a photoresist layer on the underlayer coating,

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light, and

developing the photoresist layer after the exposure to ~~light-light~~, wherein the underlayer forming composition comprises:

a polymer compound produced by addition polymerization having an epoxy group;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; and

a solvent,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

14. (Original) The method for forming photoresist pattern according to claim 13, wherein the exposure to light is carried out with a light of a wavelength of 248 nm, 193 nm or 157 nm.